

## 1 Scope

The present specifications shall apply to an FMN-1056S

## 2 Outline

Type	Silicon Diode
Structure	Resin Molded      Flammability : UL94V-0 (Equivalent)
Applications	High Frequency Rectification

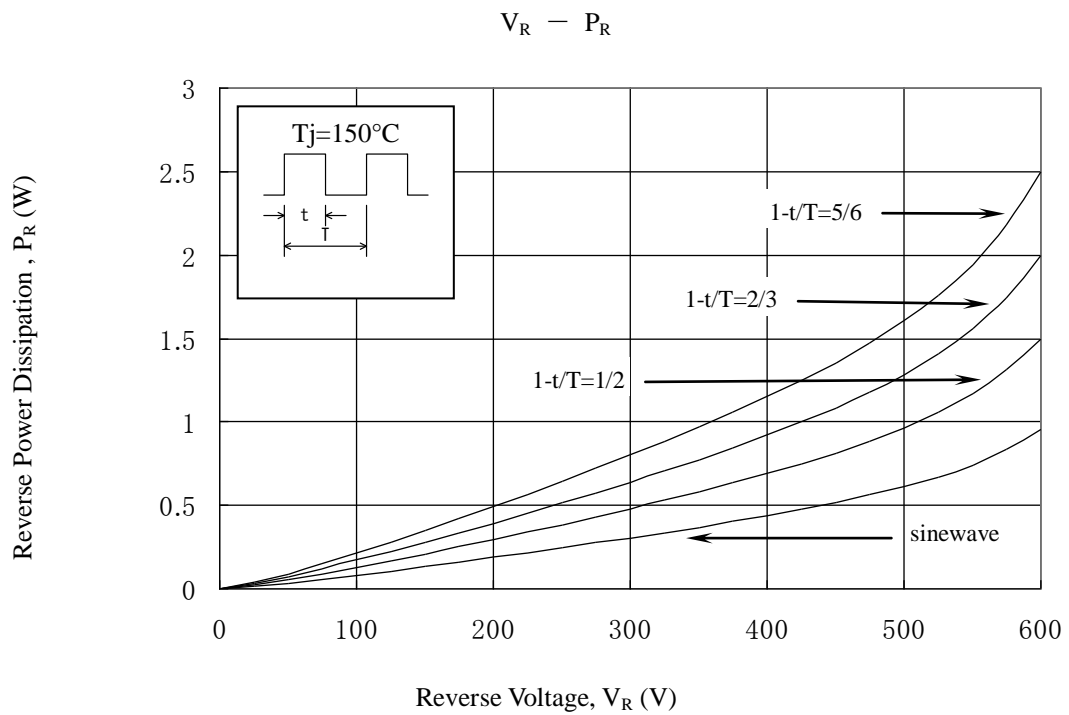
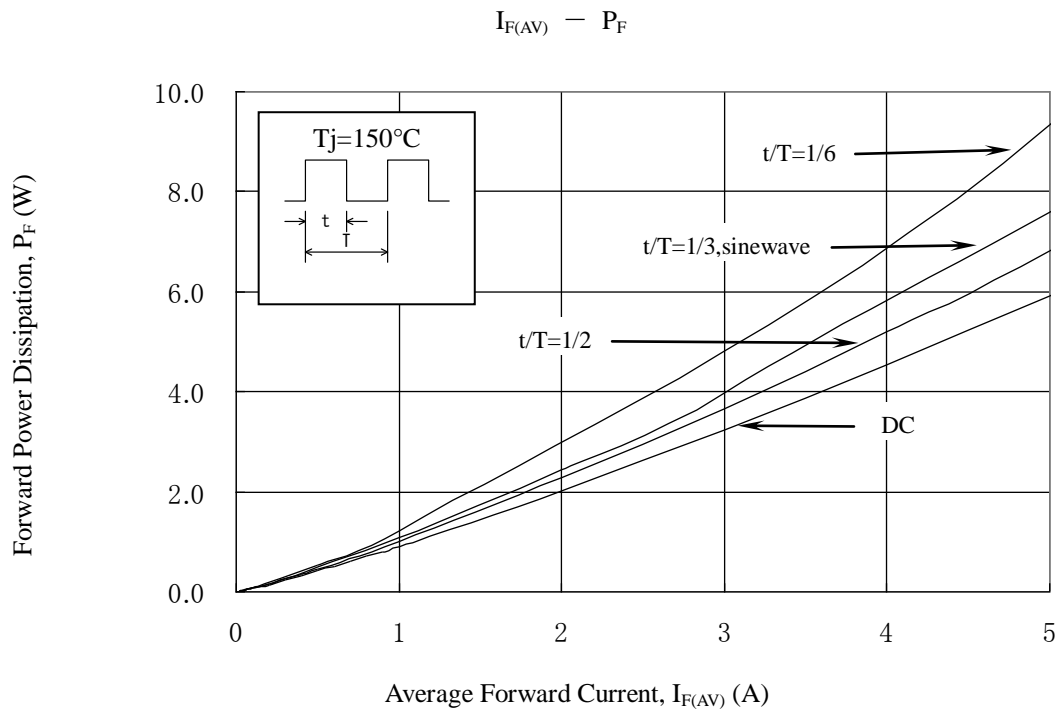
## 3 Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	$V_{RSM}$	V	600	
2	Peak Reverse Voltage	$V_{RM}$	V	600	
3	Average Forward Current	$I_{F(AV)}$	A	5	Refer to derating curve in Section 6
4	Peak Surge Forward Current	$I_{FSM}$	A	60	10ms. Half sine wave, one shot
5	$I^2t$ Limiting Value	$I^2t$	$A^2s$	18.0	$1ms \leq t \leq 10ms$
6	Junction Temperature	$T_j$	$^{\circ}C$	-40 to +150	
7	Storage Temperature	$T_{stg}$	$^{\circ}C$	-40 to +150	

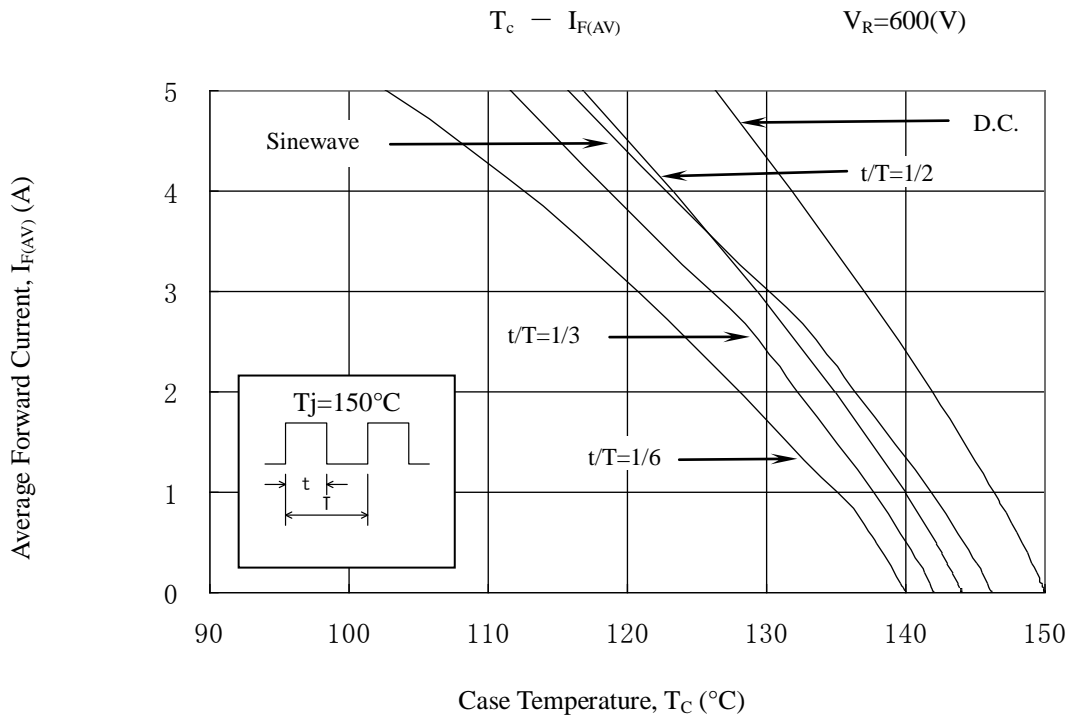
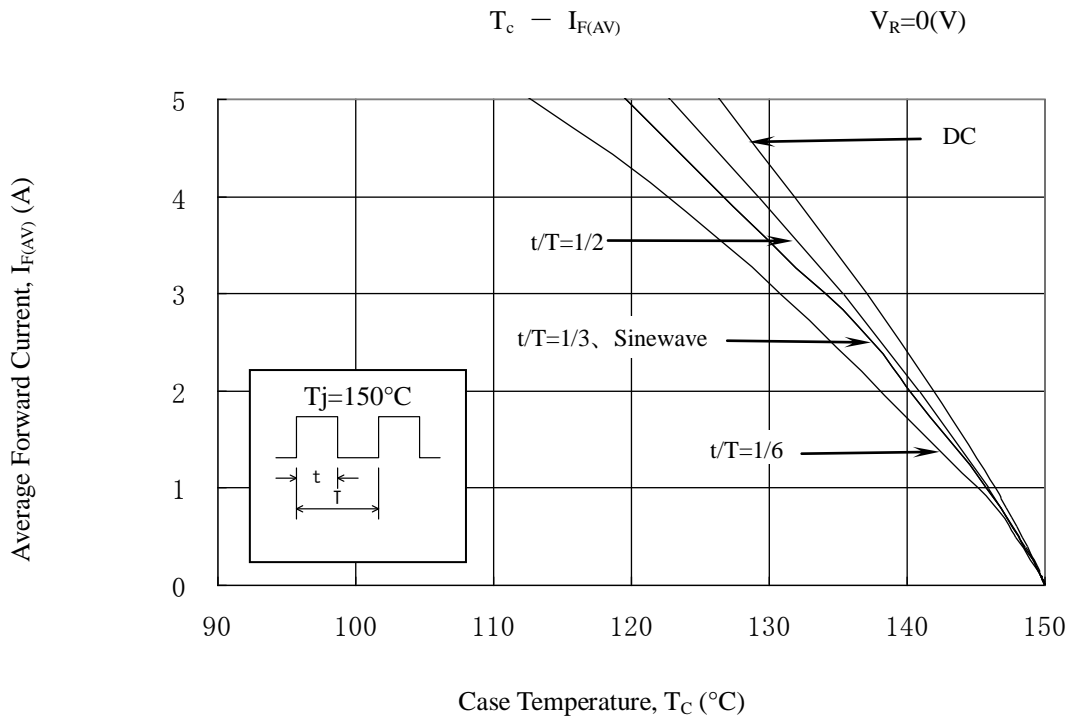
4 Electrical characteristics ( $T_a=25^{\circ}C$ , unless otherwise specified)

No.	Item	Symbol	Unit	Rating	Conditions
1	Forward Voltage Drop	$V_F$	V	1.3 max.	$I_F=5A$
2	Reverse Leakage Current	$I_R$	$\mu A$	50 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	5 max.	$V_R=V_{RM}, T_j=150^{\circ}C$
4	Reverse Recovery Time	trr1	ns	100 max.	$I_F=I_{RP}=500mA$ 90% Recovery point, $T_j=25^{\circ}C$
		trr2	ns	50 max.	$I_F=0.5A, I_{RP}=1A$ 75% Recovery point, $T_j=25^{\circ}C$
5	Thermal Resistance	$R_{th(j-c)}$	$^{\circ}C/W$	4.0 max.	Between Junction and case

5 Characteristics

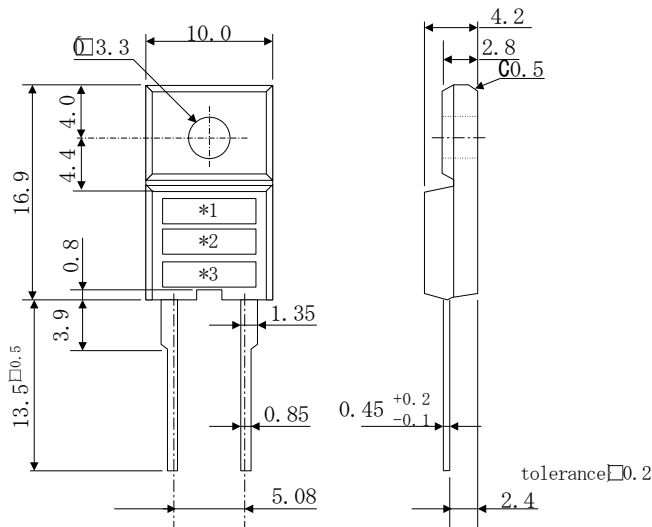


6 Derating



7 Package information

7-1 Package type, physical dimensions and material



Dimensions in mm

7-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

7-3 Marking

Type Name	Marking		
	*1 is type name	*2 is polarity	*3 is lot number
FMN-1056S	N1056	S	1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 5O17 (Oct. 17, 2005)